

Superconducting properties of nanocrystalline MgB_2 thin films made by an *in situ* annealing process

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We have studied the structural and superconducting properties of MgB_2 thin films made by pulsed laser deposition followed by *in situ* annealing. The cross-sectional transmission electron microscopy reveals a nanocrystalline mixture of textured MgO and MgB_2 with very small grain sizes. A zero-resistance transition temperature (T_{c0}) of 34 K and a zero-field critical current density (J_c) of 1.3×10^6 A/cm² were obtained. The irreversibility field was ~ 8 T at low temperatures, although severe pinning instability was observed. These bulk-like superconducting properties show that the *in situ* deposition process can be a viable candidate for MgB_2 Josephson junction technologies.

Besides its potential for high-current and high-field applications, the newly discovered superconductor MgB_2 ^{1,2} has also stimulated great interest in its applications in microelectronics. It has been shown that MgB_2 is a phonon-mediated BCS superconductor³ with an energy gap of 5.2 meV at 4.2 K⁴ and a coherence length of 50 Å.⁵ Its grain boundaries do not have large detrimental effects on superconducting current transport.^{6,7} These properties promise that Josephson junctions of MgB_2 may be much easier to fabricate than those made from the high temperature superconductors. Such junctions could have the performance of conventional superconductor junctions, such as Nb and NbN, but operate at a much higher temperature.

A MgB_2 film processing technique compatible with multilayer depositions is needed for Josephson junction applications. Currently, two main types of deposition processes have been used. The first type employs *ex situ* annealing of low-temperature deposited B or Mg+B films at 900 °C in Mg vapor. The resultant films exhibit bulk-like $T_{c0} \sim 39$ K^{8,9,10} and extremely high critical current density ($\sim 10^7$ A/cm² at low temperatures).^{11,12} However, the high-temperature *ex situ* annealing is unlikely to be compatible with multilayer device fabrications. The second type uses an *in situ* two-step process. Thin films or multilayers of Mg+B or Mg+ MgB_2 are deposited at low temperatures, and then annealed *in situ* in the deposition chamber at about 600 °C.^{8,13,14,15} Although this process is potentially more compatible with junction fabrications, the early reports from various groups on *in situ* MgB_2 thin films show lower T_{c0} around or below 25 K.^{8,13,14,15} In this paper we report that high T_{c0} and

J_c can be obtained in thin films made by an *in situ* process using pulsed laser deposition (PLD) from a single target. The structural and superconducting properties of these films as compared to the *ex situ* annealed films and polycrystalline bulk samples are discussed.

The MgB_2 films were deposited on (0001) Al_2O_3 substrates by PLD with an *in situ* annealing procedure similar to those described by Blank *et al.*,¹³ Christen *et al.*,¹⁴ and Shinde *et al.*⁸. The PLD targets were prepared by pressing Mg powder with B or MgB_2 powder at room temperature. Some targets were wrapped in Nb foil and sintered at 600 °C for 30 min under a mixed gas of 95% Ar 5% H_2 . Although both targets yielded comparable films, the results reported in this paper were from an unsintered target with a Mg: MgB_2 molar ratio of 4:1. The films were deposited at 250 - 300 °C in an Ar atmosphere (99.999% gas purity) of 120 mTorr. The background vacuum was in the low to mid 10^{-7} Torr range. The energy density of the laser beam was 5 J/cm² and the repetition rate was 5 Hz. The deposited films were then heated at a rate of 40 °C/minute to 630 °C and held there for 10 minutes. The atmosphere during the heating and annealing was the same as during the deposition. After the *in situ* annealing, the films were cooled to room temperature in ~ 20 Torr Ar. The structure of the films were studied by both x-ray diffraction and cross-sectional transmission electron microscopy (TEM). TEM studies were performed in a JEOL 4000 EX microscope operated at 400 kV, providing a point-to-point resolution of 0.17 nm.

In contrast to *ex situ* annealed MgB_2 films, x-ray diffraction scans of our *in situ* annealed films revealed no discernable film peaks, indicating that the grain size

was appreciably smaller. This is corroborated by the TEM results shown in Fig. 1. The dark field image in Fig. 1(a) shows that the film consists of two layers showing different contrast. Fig. 1(b) is a selected-area electron diffraction pattern taken from region I near the film/substrate interface. By measuring the position and intensity distribution of the diffraction rings, it is determined that they all belong to the rock salt MgO phase. The MgO crystallites are very small and textured. Fig. 1(c) is a diffraction pattern taken from region II close to the film surface using the same size selected-area aperture as for Fig. 1(b). In addition to the diffraction rings corresponding to the MgO phase, it also shows diffraction spots corresponding to the hexagonal MgB₂ phase. The diffraction spots indicated by the circles are due to the (001) planes, while those by the arrow heads arise from diffraction by the (110) planes of MgB₂. The (021) MgB₂ reflections are also detected. The discrete spots appear in Fig. 1(c) instead of nearly continuous rings in Fig. 1(b), indicating a larger grain size in region II. In both regions, the result indicates substantial oxygen contamination in the film. The MgB₂ grain size in region I must be less than about 5 nm to account for the absence of MgB₂ rings or spots in Fig. 1(b). Additional details on the microstructural analysis will be published elsewhere.

In Fig. 2(a) we plot the resistivity versus temperature curve for a 4000 Å-thick MgB₂ film. It shows a metallic behavior with a residual resistance ratio, $RRR = R(300\text{K})/R(4\text{K})$, of 1.4 and the resistivity at room temperature is $\sim 150 \mu\Omega\cdot\text{cm}$. Compared to high-density bulk samples, where $RRR = 25.3$ and $\rho(300\text{K}) = 9.6 \mu\Omega\cdot\text{cm}$,¹⁶ the residual resistance ratio of the MgB₂ film is much smaller and the resistivity much higher. This is likely due to the small grain sizes and existence of MgO in the film, since precipitates of MgO at the grain boundaries will act as series-connected resistors to the MgB₂ grains. The superconducting transition temperature of the film, on the other hand, is close to that of bulk MgB₂. The zero resistance temperatures of the film is 34 K, which is shown more clearly in the inset of the figure. The superconducting transition is further characterized by the ac susceptibility, the result of which is shown in Fig. 2(b). The transition is relatively sharp with a full width at the half maximum of the imaginary-part signal being $\sim 0.8\text{ K}$, which is comparable to that found in the bulk.¹⁶

The critical current densities of the MgB₂ films were determined using the standard Bean model¹⁷ from dc magnetization curves measured with a Quantum Design PPMS magnetometer. In Fig. 3, the temperature dependence of J_c is plotted for a 4000 Å-thick MgB₂ film. A zero-field $J_c \sim 1.34 \times 10^6 \text{ A/cm}^2$ was obtained at 7.5 K. The $M - H$ loop at 10 K for magnetic field $\mathbf{H} \perp$ film surface, which is 5 mm \times 4 mm in size, is shown in the inset. It shows a severe instability in flux pinning, or flux jump, which causes the collapse of circulating critical current so that the magnetization curve returns to the reversible magnetization branch (in the II and IV quad-

rants). The pinning instability is absent when $\mathbf{H} \parallel$ film surface, but the small film thickness yields erroneously large J_c values from the critical-state model. The actual closing of the hysteresis curve excluding the flux jump occurs at a field of $\sim 8\text{ T}$ at low temperatures, suggesting an irreversibility field similar to that found in bulk MgB₂.⁶

The T_{c0} value reported here is much higher than those in the early reports of *in situ* MgB₂ thin films.^{8,13,14,15} This demonstrates that *in situ* annealed MgB₂ films can have T_{c0} values close to those of the bulk. The critical current density ($\sim 10^6 \text{ A/cm}^2$) is also close to those of bulk MgB₂.^{5,6} These bulk-like superconducting properties suggest that although the electron diffraction patterns in Fig. 1 are dominated by the MgO features, the MgB₂ phase is formed during the *in situ* annealing process. The MgB₂ grains are believed to be very small ($\leq 5\text{ nm}$), so that their diffraction spots are not seen in region I (Fig. 1(b)) and weak in region II (Fig. 1(c)).

Compared to the *ex situ* annealed films, which are textured^{8,9,11} and have a grain size of order 10 nm¹¹, J_c in our films is an order of magnitude lower.^{10,11,12} This, as well as the slightly lower T_c and the severe pinning instability may be attributed to the small grain size in the *in situ* annealed films. When the grain size is close to the coherence length of MgB₂, the superconducting properties may be affected. While the 900 °C annealing in the *ex situ* process provides enough thermal energy for crystallization and texturing, the lower temperature during the *in situ* annealing limits the extent of these processes. The film deposited at 250 - 300 °C was likely a mixture of Mg and amorphous MgB₂ or B, and the MgB₂ crystallites were formed during the heating and annealing steps. In this annealing step, the film thickness changed from $\sim 8000\text{ Å}$ to $\sim 4000\text{ Å}$ indicating the evaporation of excess Mg and possible decomposition of MgB₂. The annealing temperature and time are constrained by the thermodynamics¹⁸ and kinetic barriers¹⁹ of the Mg-B system. The fabrication of high-quality *in situ* annealed films requires a delicate balance between the MgB₂ phase formation and decomposition.

In conclusion, we have deposited MgB₂ thin films by pulsed laser deposition using an *in situ* annealing process. The T_{c0} obtained is much higher than the previously reported *in situ* films and J_c is comparable to those of the polycrystalline bulk samples even though the grain size in the films is extremely small. Because this deposition process is more compatible with multilayer deposition, it is important to demonstrate that high T_{c0} and J_c can be obtained using this process. Our results show that it can be a viable candidate for MgB₂ Josephson junction technologies.

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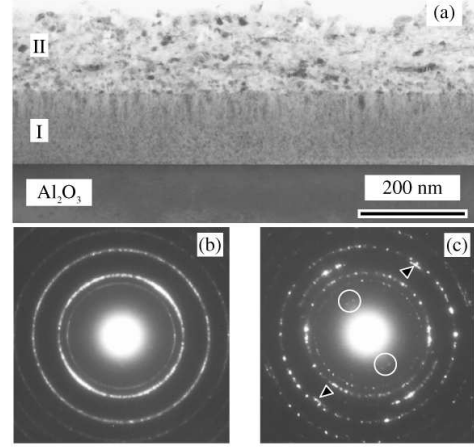


FIG. 1: (a) Dark-field TEM image showing a cross-sectional view of a MgB_2 thin films. Selected-area electron diffraction patterns from (b) region I and (c) region II.

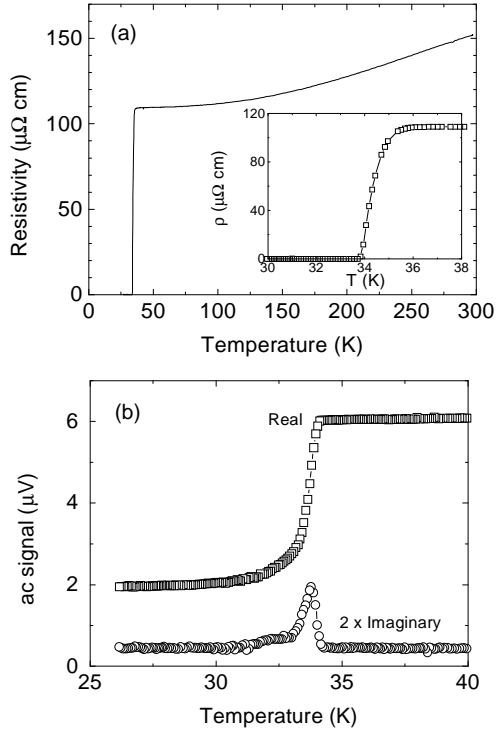


FIG. 2: (a) Resistivity versus temperature curve for a 4000 Å-thick MgB_2 film. (b) The ac susceptibility of the same film.

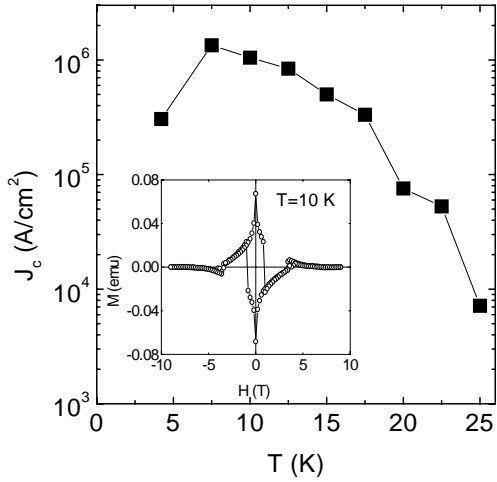


FIG. 3: The temperature dependence of the zero-field J_c of a 4000 Å-thick MgB_2 film. The inset shows the $M - H$ loop at $T = 10 \text{ K}$.